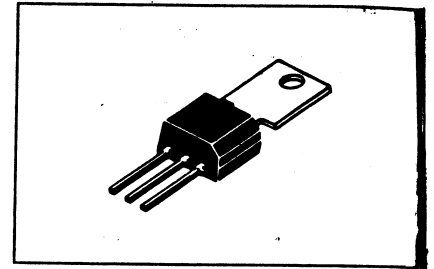


New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
 SPRINGFIELD, NEW JERSEY 07081
 U.S.A.

TELEPHONE: (201) 376-2922
 (212) 227-6005
 FAX: (201) 376-8960

MAXIMUM RATINGS					
Rating	Symbol	2N6554	2N6555	2N6556	Unit
*Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
*Collector-Base Voltage	V_{CBO}	60	80	100	Vdc
*Emitter-Base Voltage	V_{EBO}	← 5.0 →			Vdc
*Collector Current – Continuous Peak	I_C	← 1.0 →			Adc
		← 2.0 →			
*Base Current	I_B	← 100 →			mAdc
*Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	← 2.0 →			Watts
		← 16 →			mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	← 10 →			Watts
		← 80 →			mW/ $^\circ\text{C}$
*Operating and Storage Junction Temperature Range	T_J, T_{stg}	← 55 to +150 →			$^\circ\text{C}$
*Solder Temperature, 1/16" from Case for 10 Seconds	—	← 260 →			$^\circ\text{C}$
THERMAL CHARACTERISTICS					
Characteristic	Symbol	Max	Unit		
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$		
Thermal Resistance, Junction to Case	$R_{\theta JC}$	12.5	$^\circ\text{C/W}$		



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	BV_{CEO}	60 80 100	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	BV_{CBO}	60 80 100	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}, I_C = 0$)	BV_{EBO}	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40 \text{ Vdc}, I_E = 0$) ($V_{CB} = 60 \text{ Vdc}, I_E = 0$) ($V_{CB} = 80 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	100 100 100	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 250 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	60 80 60 25	— 300 — —	
Collector-Emitter Saturation Voltage ($I_C = 250 \text{ mAdc}, I_B = 10 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$)	$V_{CE(sat)}$	—	0.5 1.0	Vdc
Base Emitter On Voltage ($I_C = 250 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(on)}$	—	1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain – Bandwidth Product ($I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}, f = 20 \text{ MHz}$)	f_T	75	375	MHz
Collector-Base Capacitance ($V_{CB} = 20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{cb}	—	18	pF

* Indicates JEDEC Registered Data.

** Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.



Quality Semi-Conductors